STQ2NF06L

N-CHANNEL 60V - 0.1 Ω - 2A TO-92
STripFET™ II POWER MOSFET

| TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STQ2NF06L	60 V	<0.12 Ω	2 A

■ TYPICAL R_{DS}(on) = 0.1 Ω
■ EXTREMELY HIGH dv/dt CAPABILITY
■ 100% AVALANCHE TESTED
■ AVALANCHE RUGGED TECHNOLOGY
■ LOW THRESHOLD DRIVE

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronis unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

■ DC MOTOR CONTROL (DISK DRIVES, etc.)
■ DC-DC & DC-AC CONVERTERS
■ SYNCHRONOUS RECTIFICATION

TO-92 **TO-92 (Ammopack)**
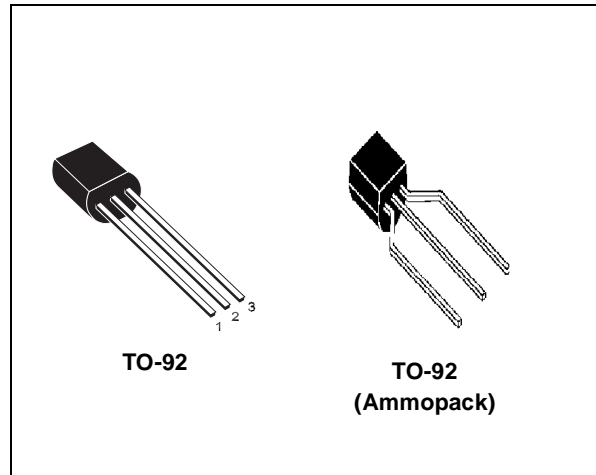
INTERNAL SCHEMATIC DIAGRAM

SC06140Iv
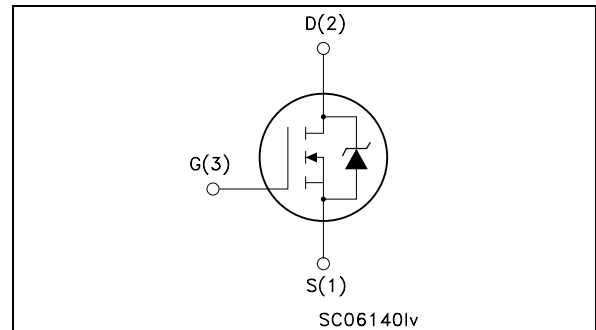
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	60	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	60	V
V_{GS}	Gate- source Voltage	± 16	V
I_D	Drain Current (continuous) at T_C = 25°C	2	A
I_D	Drain Current (continuous) at T_C = 100°C	1.2	A
I_{DM}(•)	Drain Current (pulsed)	8	A
P_{tot}(1)	Total Dissipation at T_C = 25°C	3	W
	Derating Factor	8	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	6	V/ns
E_{AS} (3)	Single Pulse Avalanche Energy	200	mJ
T_{stg}	Storage Temperature	-55 to 150	°C
T_j	Max. Operating Junction Temperature		°C

(•) Pulse width limited by safe operating area.
(1) Related to Rthj -l

(2) I_{SD} ≤2A, di/dt ≤100A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}
(3) Starting T_j = 25 ºC, I_D = 2A, V_{DD} = 30V

.

THERMAL DATA

Rthj-lead	Thermal Resistance Junction-Lead	Max	40	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	125	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	Typ	260	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	60			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_C = 125°C			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 16 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	1			V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 1 A V_{GS} = 5 V I_D = 1 A		0.1 0.12	0.12 0.14	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	V_{DS} = 15 V I_D = 1 A		3		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V f = 1 MHz V_{GS} = 0		360 55 25		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 30 V I_D = 1 A R_G = 4.7 Ω V_{GS} = 4.5 V (Resistive Load, Figure 3)		10 20		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD}= 48 V I_D= 2 A V_{GS}= 5 V		5.6 1.2 2.6	7.6	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 30 V I_D = 1 A R_G = 4.7Ω, V_{GS} = 4.5 V (Resistive Load, Figure 3)		17 6		ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (•)	Source-drain Current Source-drain Current (pulsed)				2 8	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 2 A V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 2 A di/dt = 100A/μs V_{DD} = 20 V T_j = 150°C (see test circuit, Figure 5)		28 31 2.2		ns nC A

(*)Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.
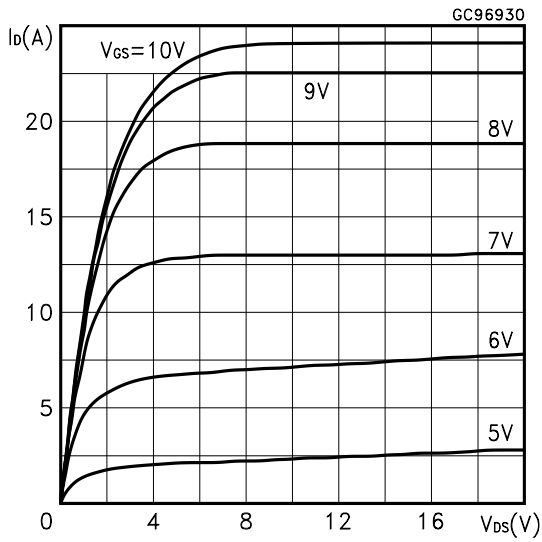(•)Pulse width limited by safe operating area.
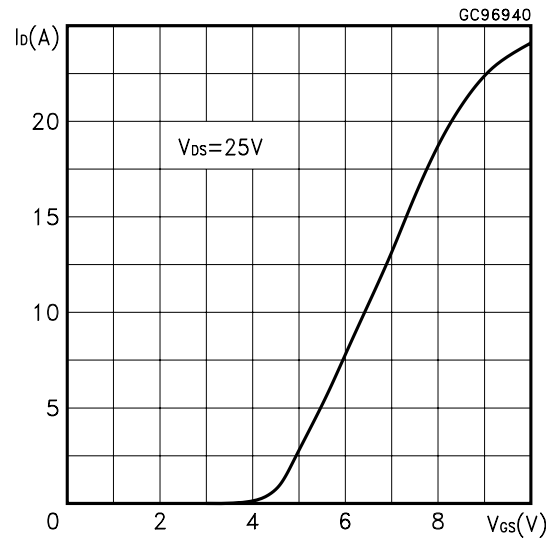
Safe Operating Area
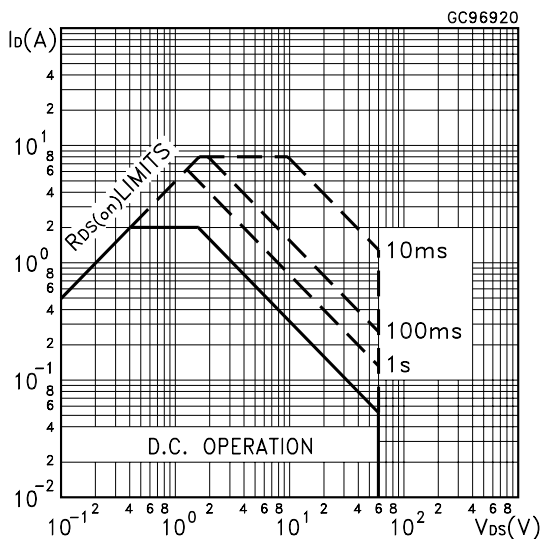
Thermal Impedance Junction-lead
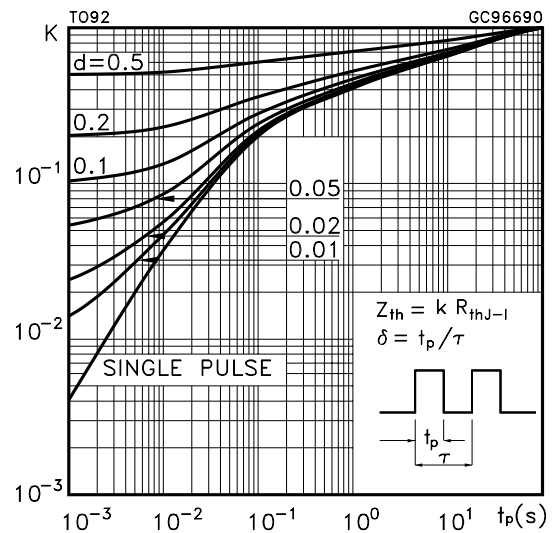
Output Characteristics

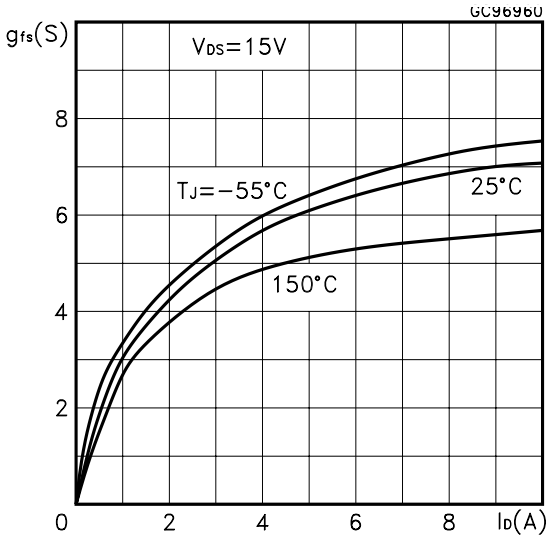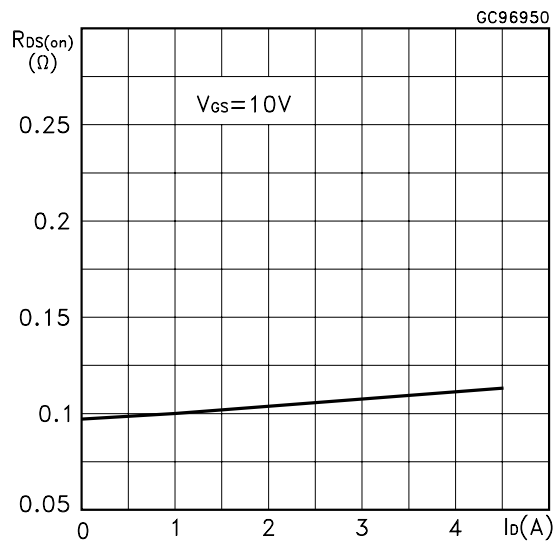GC96930

$I_D(A)$

$V_{GS}=10V$

9V

8V

7V

6V

5V

20

15

10

5

0   4   8   12   16 $V_{DS}(V)$

Transfer Characteristics

GC96940

$I_D(A)$

$V_{DS}=25V$

20

15

10

5

0   2   4   6   8 $V_{GS}(V)$

Transconductance

GC96960

$g_{fs}(S)$

$V_{DS}=15V$

$T_J=-55°C$ 25°C

150°C

8

6

4

2

0   2   4   6   8 $I_D(A)$

Static Drain-source On Resistance

GC96950

$R_{DS(on)}$ (Ω)

$V_{GS}=10V$

0.25

0.2

0.15

0.1

0.05

0   1   2   3   4 $I_D(A)$

Gate Charge vs Gate-source Voltage

GC96970

$V_{GS}(V)$

$V_{DS}=48V$
$I_D=14A$

8

6

4

2

0   3   6   9   12 $Q_g(nC)$
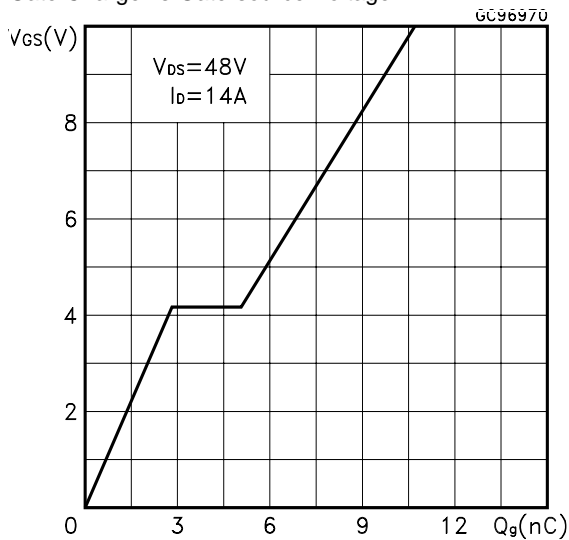
Capacitance Variations

GC96980

$C(pF)$

$f=1MHz$
$V_{GS}=0V$

C_{iss}

C_{oss}

C_{rss}

400

300

200

100

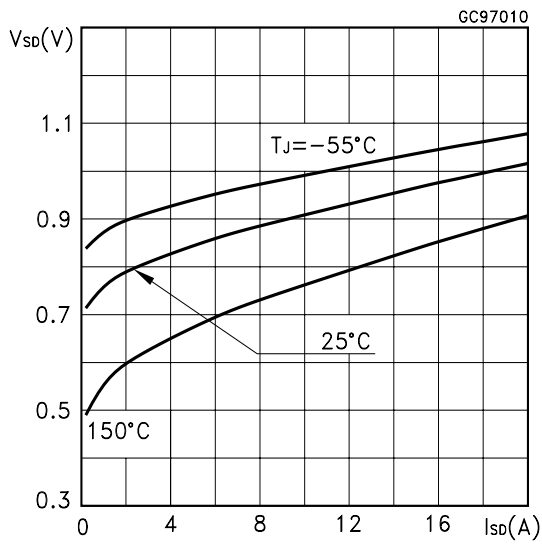0   10   20   30   40 $V_{DS}(V)$
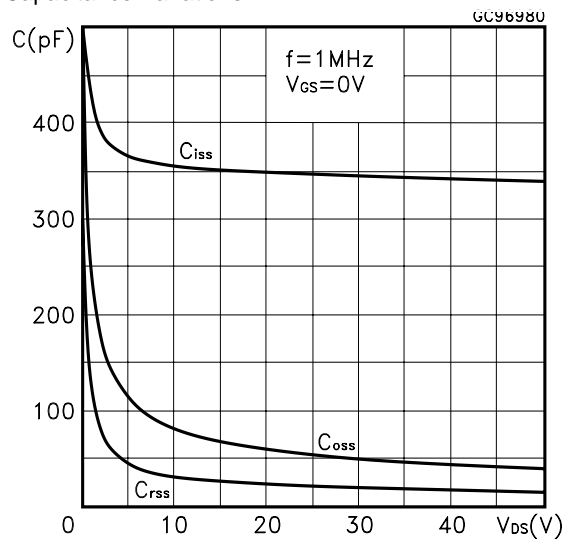
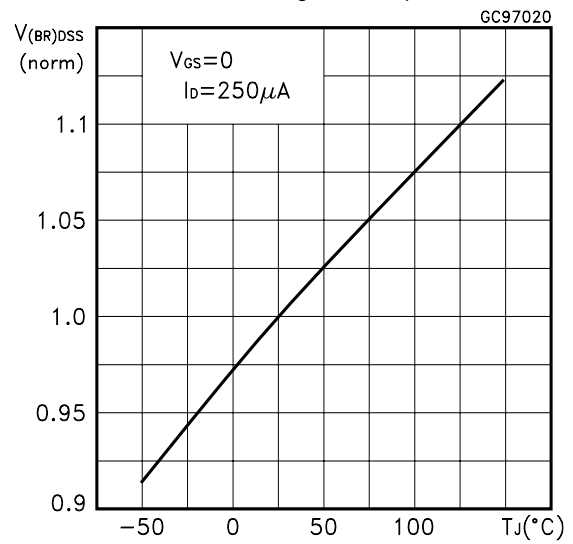Normalized Gate Threshold Voltage vs Temperature
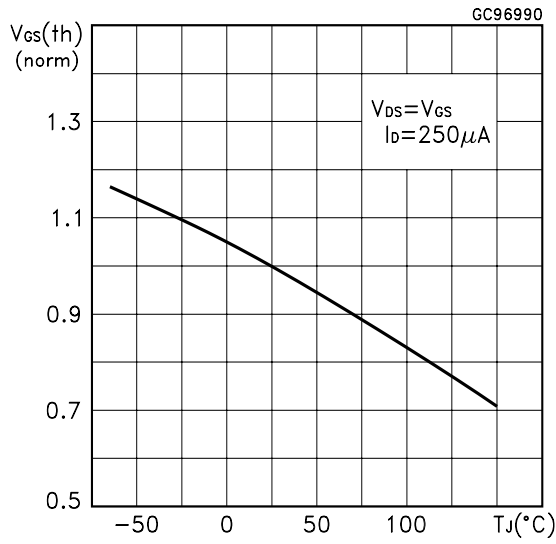
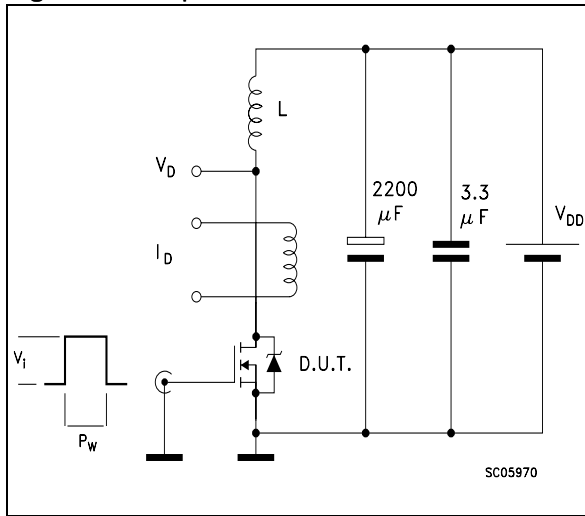Normalized on Resistance vs Temperature
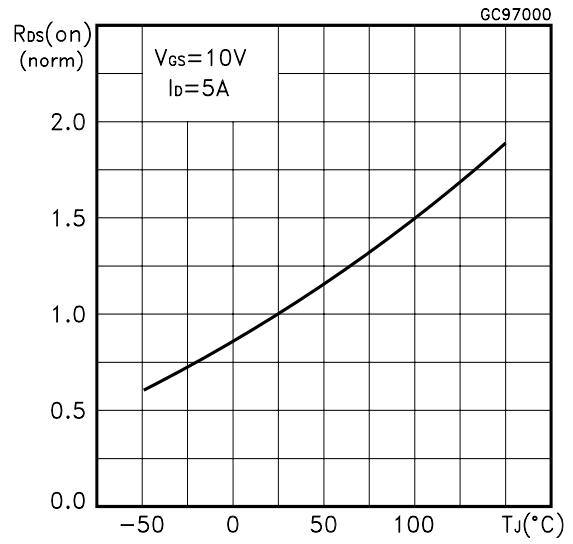
Source-drain Diode Forward Characteristics

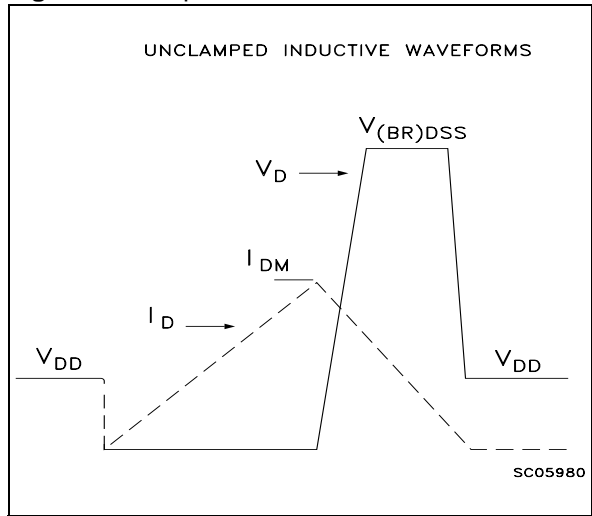Normalized Breakdown Voltage vs Temperature.

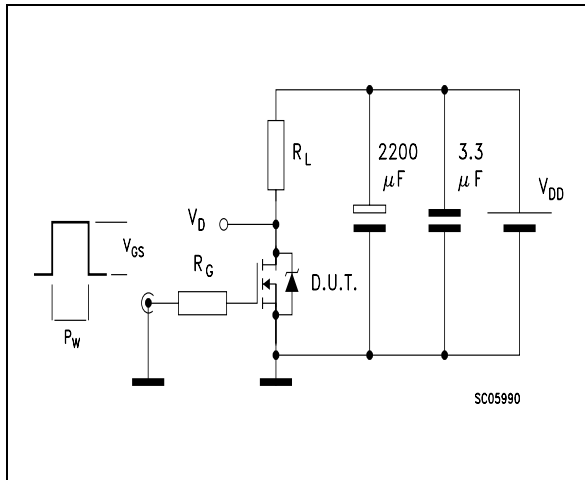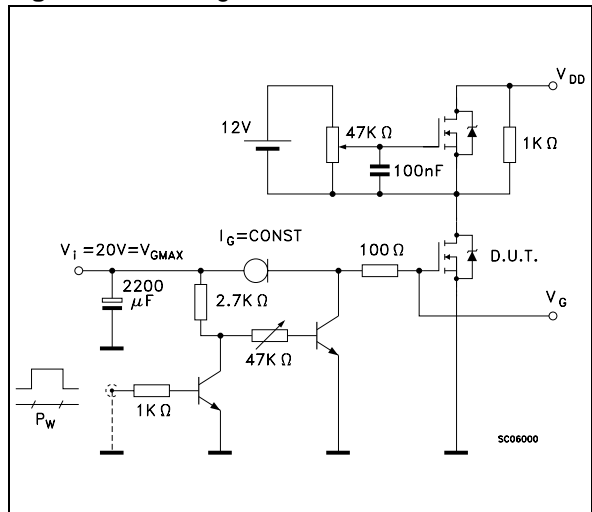**Fig. 1:** Unclamped Inductive Load Test Circuit
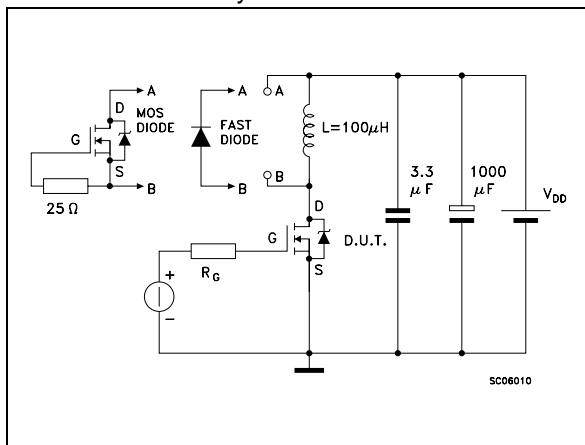

SC05970

Fig. 2: Unclamped Inductive Waveform

UNCLAMPED INDUCTIVE WAVEFORMS

SC05980

Fig. 3: Switching Times Test Circuits For Resistive Load

SC05990

Fig. 4: Gate Charge test Circuit

SC06000

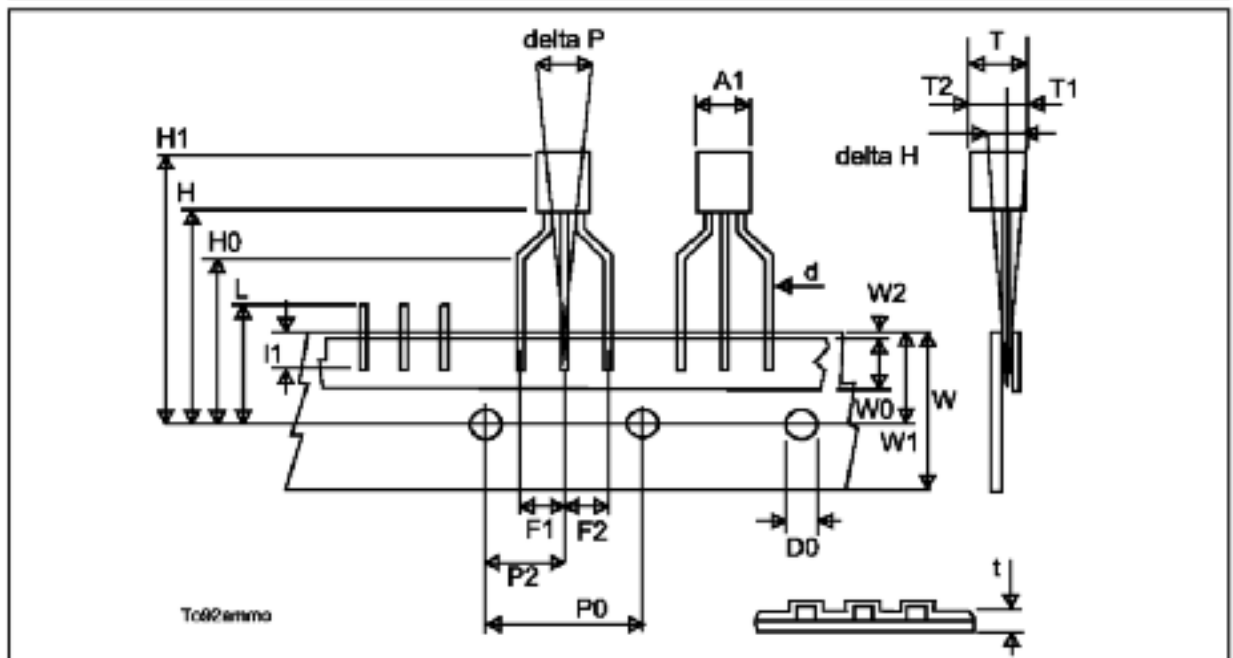**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times

SC06010

TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	**TYP.**	**MAX.**	**MIN.**	**TYP.**	**MAX.**
A	4.58		5.33	0.180		0.210
B	4.45		5.2	0.175		0.204
C	3.2		4.2	0.126		0.165
D	12.7			0.500		
E		1.27			0.050	
F	0.4		0.51	0.016		0.020
G	0.35			0.14		
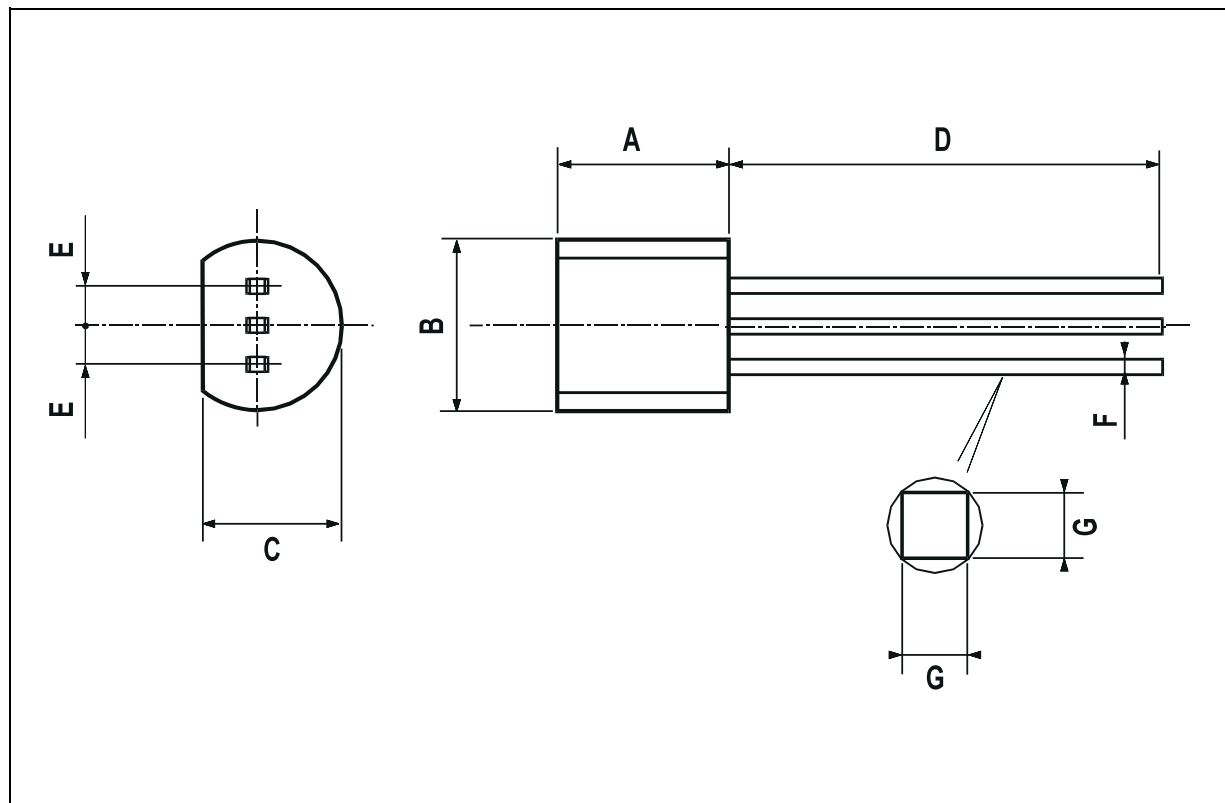
TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1			4.8			0.19
T			3.8			0.15
T1			1.6			0.06
T2			2.3			0.09
d			0.48			0.02
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
l1	3			0.11		
delta P	-1		1	-0.04		0.04

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